

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of:

Docket No. P27157

Haujie CHEN, *et al.*

Confirmation No. 4303

Appln. No. : 10/689,506

Group Art Unit: 2813

Filed : October 20, 2003

Examiner: J. M. Mitchell

For : HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C  
AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF  
MANUFACTURE

Commissioner for Patents  
U.S. Patent and Trademark Office  
Customer Service Window, Mail Stop Amendment  
Randolph Building  
401 Dulany Street  
Alexandria VA 22314

**SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. §1.111**

Sir:

As a supplement to the Amendment filed on April 25, 2007, Applicants request allowance of the application in view of the following amendments and remarks.

Amendments to the claims begin on page 2; and

Remarks begin on page 5.

If extensions of time are necessary to prevent abandonment of this application, then such extensions of time are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefore (including fees for net addition of claims) are hereby authorized to be charged to Deposit Account No. 09-0458.